

# FNK N-Channel Enhancement Mode Power MOSFET

#### **Description**

The FNK2300 uses advanced trench technology to provide excellent  $R_{\rm DS(ON)}$ , low gate charge and operation with gate voltages as low as 0.5V. This device is suitable for use as a Battery protection or in other Switching application.

# G S

Schematic diagram

# YKRL1

Marking and pin assignment



SOT-23 top view

#### **General Features**

•  $V_{DS} = 20V, I_D = 3A$ 

 $R_{DS(ON)}$  < 54m $\Omega$  @  $V_{GS}$ =2.5V

 $R_{DS(ON)}$  < 39m $\Omega$  @  $V_{GS}$ =4.5V

- High power and current handing capability
- Lead free product is acquired
- Surface mount package

# **Application**

- Battery protection
- Load switch
- Power management

**Package Marking and Ordering Information** 

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
YKRL1	FNK2300	SOT-23	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (T<sub>A</sub>=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	20	V
Gate-Source Voltage	V <sub>GS</sub>	±10	V
Drain Current-Continuous	I <sub>D</sub>	3	Α
Drain Current-Pulsed (Note 1)	I <sub>DM</sub>	12	А
Maximum Power Dissipation	P <sub>D</sub>	0.9	W
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 150	$^{\circ}$ C

### **Thermal Characteristic**

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	139	°C/W

#### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	20	24	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V,V <sub>GS</sub> =0V	-	-	1	μA



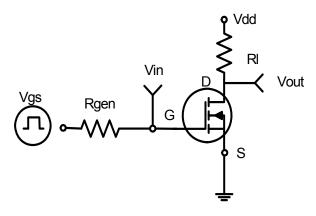
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±12V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS},I_{D}=250\mu A$	0.4	0.55	0.9	V
Drain-Source On-State Resistance	-	V <sub>GS</sub> =2.5V, I <sub>D</sub> =2.8A	-	35	54	mΩ
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =3A	-	28	39	mΩ
Forward Transconductance	<b>g</b> fs	$V_{DS}$ =5 $V$ , $I_{D}$ =3 $A$	-	8	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>lss</sub>	\/ -40\/\/ -0\/	-	260	-	PF
Output Capacitance	Coss	$V_{DS}$ =10V, $V_{GS}$ =0V, F=1.0MHz	-	48	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.UIVITIZ	-	27	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	2.5	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =10V, $R_L$ =3.3 $\Omega$	-	3.2	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =4.5 $V$ , $R_{GEN}$ =6 $\Omega$	-	21	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	3	-	nS
Total Gate Charge	Qg	\/ 40\/ L 0A	-	2.9	5	nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ =10V, $I_{D}$ =3A, $V_{GS}$ =4.5V	-	0.4	-	nC
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =4.5V	-	0.6	-	nC
Drain-Source Diode Characteristics	,		•			•
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =3.3A	-	0.75	1.2	V
Diode Forward Current (Note 2)	Is		-	-	3.3	Α

#### Notes:

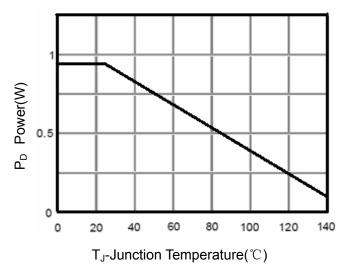
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.
- **3.** Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



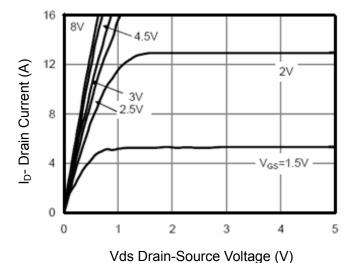
# **Typical Electrical and Thermal Characteristics**



**Figure 1:Switching Test Circuit** 



**Figure 3 Power Dissipation** 



**Figure 5 Output Characteristics** 

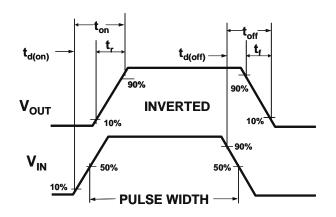
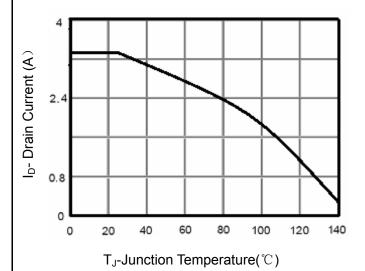


Figure 2:Switching Waveforms



**Figure 4 Drain Current** 

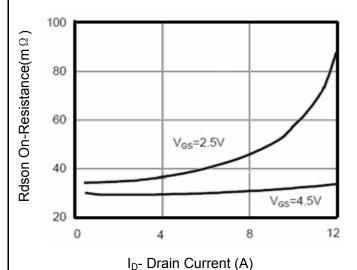


Figure 6 Drain-Source On-Resistance



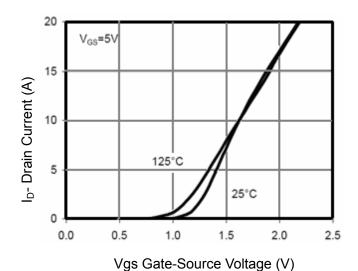


Figure 7 Transfer Characteristics

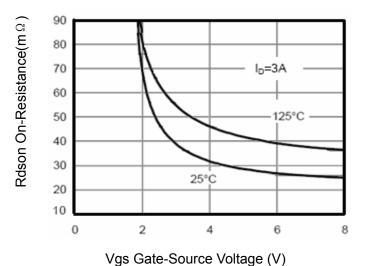
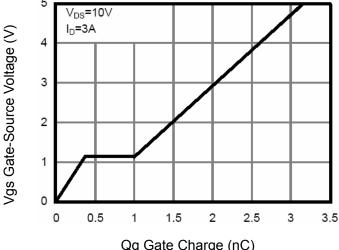
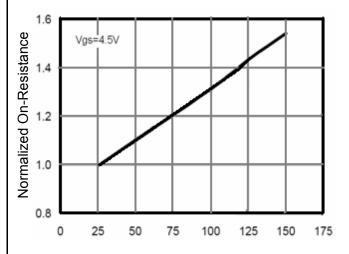


Figure 9 Rdson vs Vgs



Qg Gate Charge (nC) Figure 11 Gate Charge



T<sub>J</sub>-Junction Temperature(℃)

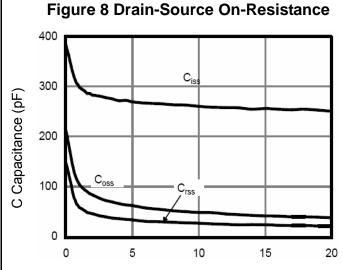
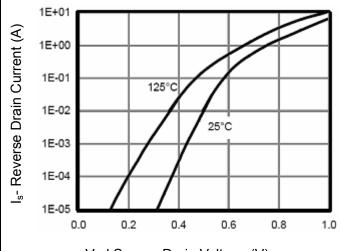


Figure 10 Capacitance vs Vds

Vds Drain-Source Voltage (V)



Vsd Source-Drain Voltage (V)

Figure 12 Source- Drain Diode Forward



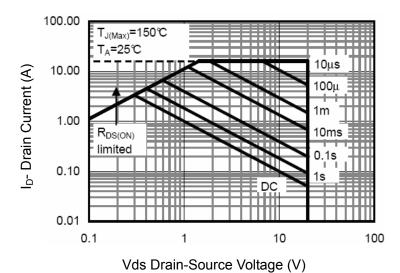
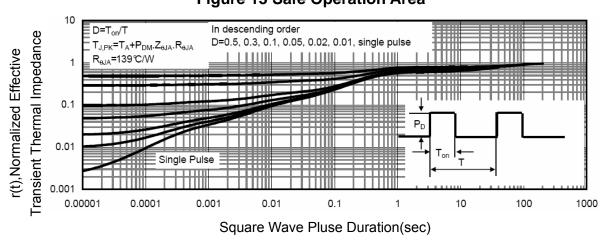


Figure 13 Safe Operation Area



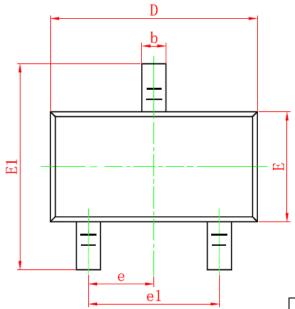
**Figure 14 Normalized Maximum Transient Thermal Impedance** 

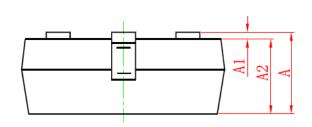
FNK-Semiconductor 5/7 Rev.1.1

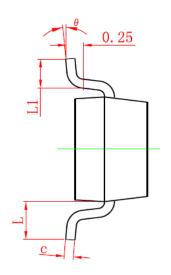


# **SOT-23 PACKAGE INFORMATION**

## **Dimensions in Millimeters (UNIT:mm)**







Symbol	Dimensions in Millimeters			
	MIN.	MAX.		
Α	0.900	1.150		
A1	0.000	0.100		
A2	0.900	1.050		
b	0.300	0.500		
С	0.080	0.150		
D	2.800	3.000		
E	1.200	1.400		
E1	2.250	2.550		
е	0.950TYP			
e1	1.800	2.000		
L	0.550REF			
L1	0.300	0.500		
θ	0°	8°		

#### **NOTES**

- 1. All dimensions are in millimeters.
- 2. Tolerance ±0.10mm (4 mil) unless otherwise specified
  3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
  5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.



#### ATTENTION:

- FNK reserves the right to make changes to the information herein for the improvement of the design and performance without further notice! Customers should obtain the latest relevant information before placing orders and should verify that such information is complete and current.
- FNK assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all FNK products described or contained herein.
- Specifications of any and all FNK products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- FNKstrives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all FNK products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the FNK product that you intend to use.
- FNK will supply the best possible product for customers!

FNK-Semiconductor 7/7 Rev.1.1